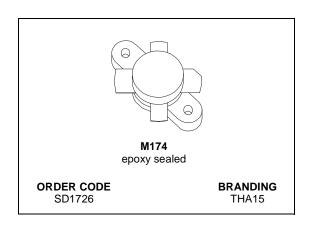


SD1726 (THA15) RF & MICROWAVE TRANSISTORS HF SSB APPLICATIONS

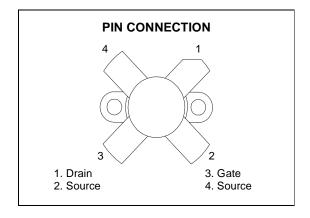
FEATURES

- OPTIMIZED FOR SSB
- 30 MHz
- 50 V
- IMD-30 dB
- COMMON EMITTER
- GOLD METALLIZATION
- P_{OUT} = 150 W PEP MIN. WITH 14 dB GAIN



DESCRIPTION

The SD1726 is a 50 V epitaxial silicon NPN planar transistor designed primarily SSB communications. This device utilizes emitter ballasting to achieve extreme ruggedness under severe operating conditions.



ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25 °C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collecto-Base Voltage	110	V
V _{CEO}	Collector-Emitter Voltage	55	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ic	Drain Current	20	Α
P _{DISS}	Power Dissipation	318	W
Tj	Max. Operating Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

R _{th(j-c)}	Junction -Case Thermal Resistance at T _{CASE} = 70 °C	0.75	°C/W
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ELECTRICAL SPECIFICATION (T_{CASE} = 25 °C)

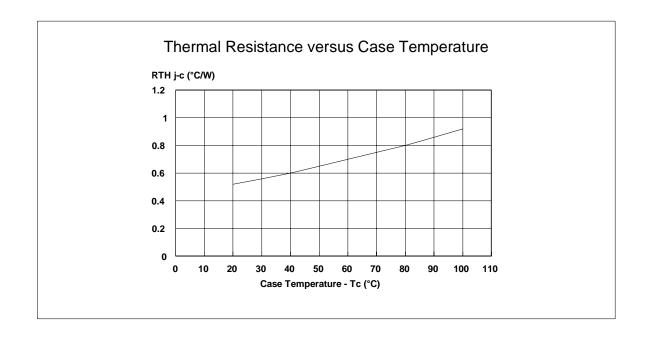
STATIC

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	I _C = 100 mA I _E = 0 mA	110			V
BV _{CES}	I _C = 100 mA V _{BE} = 0 V	110			V
BV _{CEO}	I _C = 100 mA I _B = 0 mA	55			V
BV _{EBO}	I _E = 10 mA I _C = 0 mA	4.0			V
I _{CEO}	V _{CE} = 30 V I _E = 0 mA			5	mA
I _{CES}	V _{CE} = 60 V I _E = 0 mA			5	mA
h _{FE}	V _{CE} = 6 V I _C = 1.4 A	18		43.5	

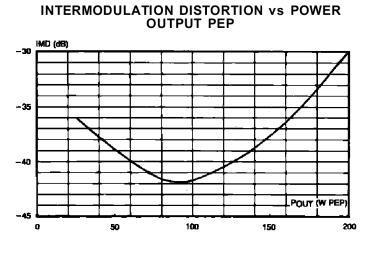
DYNAMIC

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Pout	V _{CE} = 50 V I _{CQ} = 100 mA f = 30 MHz	150			W
$G_P^{^*}$	V _{CE} = 50 V I _{CQ} = 100 mA P _{OUT} = 150 W PEP	14			dB
IMD*	V _{CE} = 50 V I _{CQ} = 100 mA P _{OUT} = 150 W PEP			-30	dBc
$\eta_{D}^{^*}$	V _{CE} = 50 V I _{CQ} = 100 mA P _{OUT} = 150 W PEP	37			%
G _{OB}	V _{CB} = 50 V f = 1 MHz			220	pF

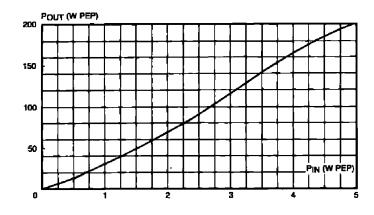
Note: The SD1726 is also usable in Class A at 40 V. Typical performance is: P_{OUT} = 30 W PEP, G_P = 14 dB, IMD = - 40 dBc * f_1 = 30.00 MHz; f_2 = 30.001 MHz



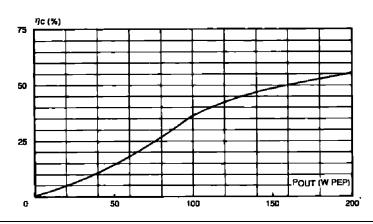
TYPICAL PERFORMANCE



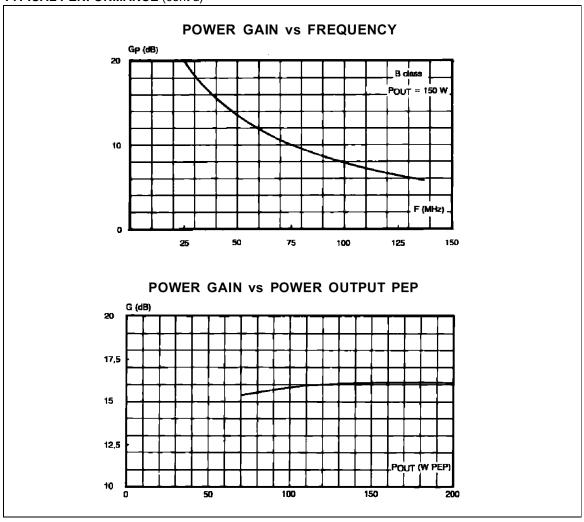
POWER OUTPUT PEP vs POWER INPUT



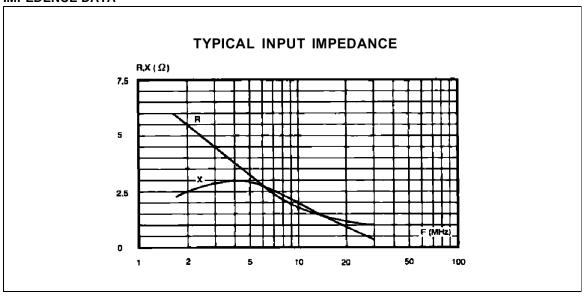
COLLECTOR EFFICIENCY vs POWER OUTPUT PEP



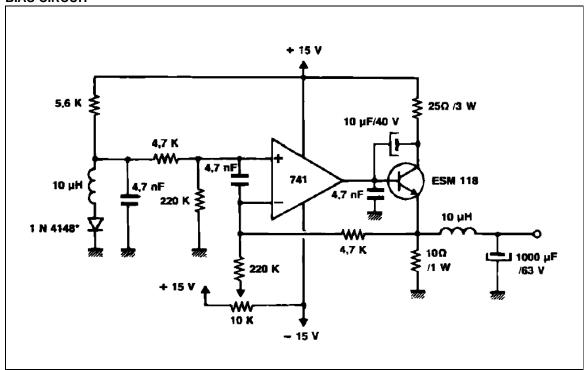
TYPICAL PERFORMANCE (cont'd)



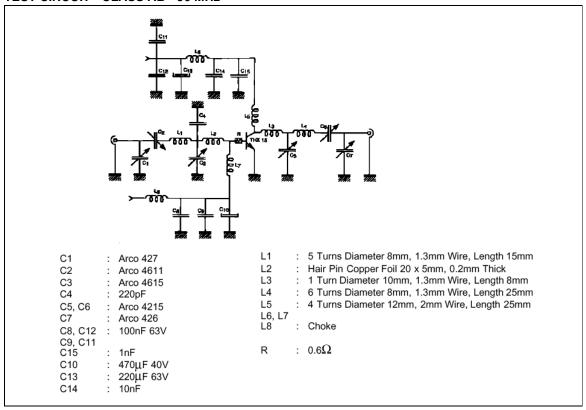
IMPEDENCE DATA



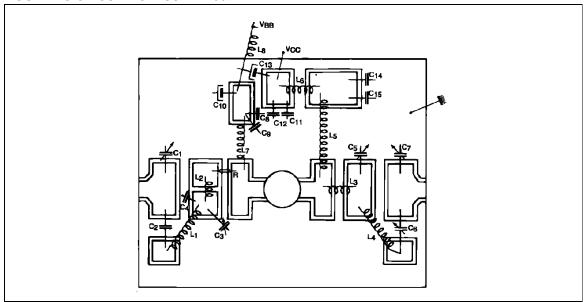
BIAS CIRCUIT



TEST CIRCUIT - CLASS AB - 30 MHz

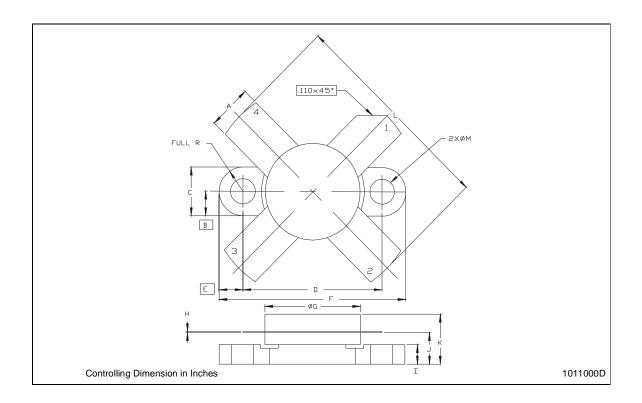


MOUNTING CIRCUIT - CLASS AB - 30 MHz



M174 (.500 DIA 4/L N/HERM W/FLG) MECHANICAL DATA

DIM.		mm			Inch	
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
А	5.56		5.584	0.219		0.230
В		3.18			0.125	
С	6.22		6.48	0.245		0.255
D	18.28		18.54	0.720		0.730
E		3.18			0.125	
F	24.64		24.89	0.970		0.980
G	12.57		12.83	0.495		0.505
Н	0.08		0.18	0.003		0.007
I	2.11		3.00	0.083		0.118
J	3.81		4.45	0.150		0.175
K			7.11			0.280
L	25.53		26.67	1.005		1.050
М	3.05		3.30	0.120		0.130



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